Abstracts

An Approximate Comparison Between n+-p-p+ and p+-n-n+ Silicon TRAPATT Diodes (Short Papers)

G.I. Haddad, C.M. Lee and W.E. Schroeder. "An Approximate Comparison Between n+-p-p+ and p+-n-n+ Silicon TRAPATT Diodes (Short Papers)." 1973 Transactions on Microwave Theory and Techniques 21.7 (Jul. 1973 [T-MTT]): 501-502.

The difference in the ionization rates of holes and electrons in Si results in different properties of n+-p-p+ and p+-n-n+ TRAPATT diodes. An approximate analysis is presented which shows these differences and indicates superior performance in the n+-p-p+ structure.

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